



# FDD86369

## N-Channel PowerTrench® MOSFET

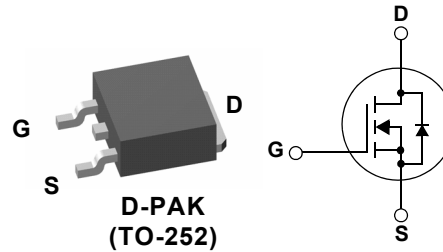
### 80 V, 90 A, 7.9 mΩ

#### Features

- Typical  $R_{DS(on)}$  = 5.9 mΩ at  $V_{GS} = 10V$ ,  $I_D = 80 A$
- Typical  $Q_g(tot)$  = 34 nC at  $V_{GS} = 10V$ ,  $I_D = 80 A$
- UIS Capability
- RoHS Compliant

#### Applications

- PowerTrain Management
- Solenoid and Motor Drivers
- Integrated Starter/Alternator
- Primary Switch for 12V Systems



For current package drawing, please refer to the ON website at <http://www.fairchildsemi.com/package-drawings/TO/TO252A03.pdf>

#### MOSFET Maximum Ratings $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Rated	Units
$V_{DSS}$	Drain-to-Source Voltage		80	V
$V_{GS}$	Gate-to-Source Voltage		±20	V
$I_D$	Drain Current - Continuous ( $V_{GS}=10$ ) (Note 1)	$T_C = 25^\circ\text{C}$	90	A
	Pulsed Drain Current	$T_C = 25^\circ\text{C}$	See Figure 4	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 2)	29	mJ
$P_D$	Power Dissipation		150	W
	Derate Above $25^\circ\text{C}$		1.0	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature		-55 to + 175	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.0	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	52	$^\circ\text{C}/\text{W}$

#### Notes:

- 1: Current is limited by bondwire configuration.
- 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 14\mu\text{H}$ ,  $I_{AS} = 64\text{A}$ ,  $V_{DD} = 80\text{V}$  during inductor charging and  $V_{DD} = 0\text{V}$  during time in avalanche.
- 3:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD86369	FDD86369	D-PAK(TO-252)	13"	16 mm	2500 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$B_{VDSS}$	Drain-to-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	80	-	-	V
$I_{DSS}$	Drain-to-Source Leakage Current	$V_{DS} = 80\text{V}, T_J = 25^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{V}, T_J = 175^\circ\text{C}$ (Note 4)	-	-	1	$\text{mA}$
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	$\text{nA}$

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2.0	2.7	4.0	V
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}, T_J = 25^\circ\text{C}$	-	5.9	7.9	$\text{m}\Omega$
		$V_{GS} = 10\text{V}, T_J = 175^\circ\text{C}$ (Note 4)	-	13.0	17.4	$\text{m}\Omega$

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	2530	-	$\text{pF}$
$C_{oss}$	Output Capacitance		-	430	-	$\text{pF}$
$C_{riss}$	Reverse Transfer Capacitance		-	16	-	$\text{pF}$
$R_g$	Gate Resistance	$V_{GS} = 0.5\text{V}, f = 1\text{MHz}$	-	2.2	-	$\Omega$
$Q_{g(ToT)}$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$	-	36	54	$\text{nC}$
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2\text{V}$				
$Q_{gs}$	Gate-to-Source Gate Charge	$V_{DD} = 64\text{V}, I_D = 80\text{A}$	-	13	-	$\text{nC}$
$Q_{gd}$	Gate-to-Drain "Miller" Charge		-	8.5	-	$\text{nC}$

**Switching Characteristics**

$t_{on}$	Turn-On Time	$V_{DD} = 40\text{V}, I_D = 80\text{A}, V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$	-	-	70	$\text{ns}$
$t_{d(on)}$	Turn-On Delay		-	13	-	$\text{ns}$
$t_r$	Rise Time		-	34	-	$\text{ns}$
$t_{d(off)}$	Turn-Off Delay		-	22	-	$\text{ns}$
$t_f$	Fall Time		-	9	-	$\text{ns}$
$t_{off}$	Turn-Off Time		-	-	46	$\text{ns}$

**Drain-Source Diode Characteristics**

$V_{SD}$	Source-to-Drain Diode Voltage	$I_{SD} = 80\text{A}, V_{GS} = 0\text{V}$	-	-	1.25	V
		$I_{SD} = 40\text{A}, V_{GS} = 0\text{V}$	-	-	1.2	V
$t_{rr}$	Reverse-Recovery Time	$I_F = 80\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	49	64	$\text{ns}$
$Q_{rr}$	Reverse-Recovery Charge		-	40	53	$\text{nC}$

**Note:**

4: The maximum value is specified by design at  $T_J = 175^\circ\text{C}$ . Product is not tested to this condition in production.

### Typical Characteristics

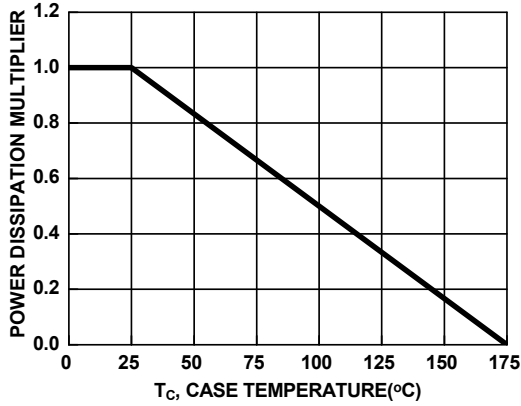


Figure 1. Normalized Power Dissipation vs. Case Temperature

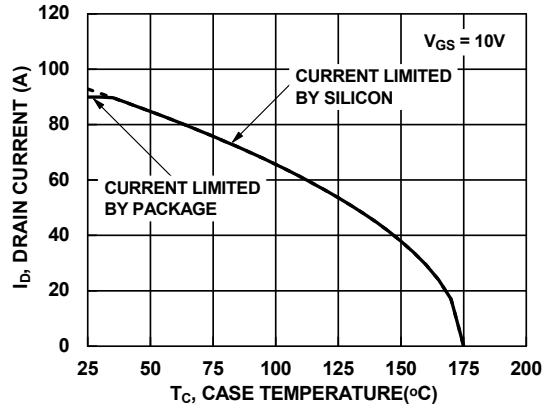


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

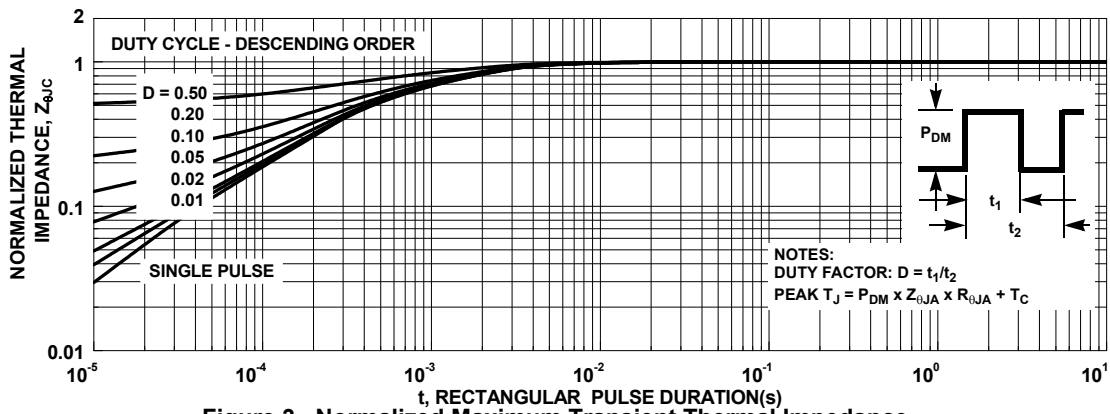


Figure 3. Normalized Maximum Transient Thermal Impedance

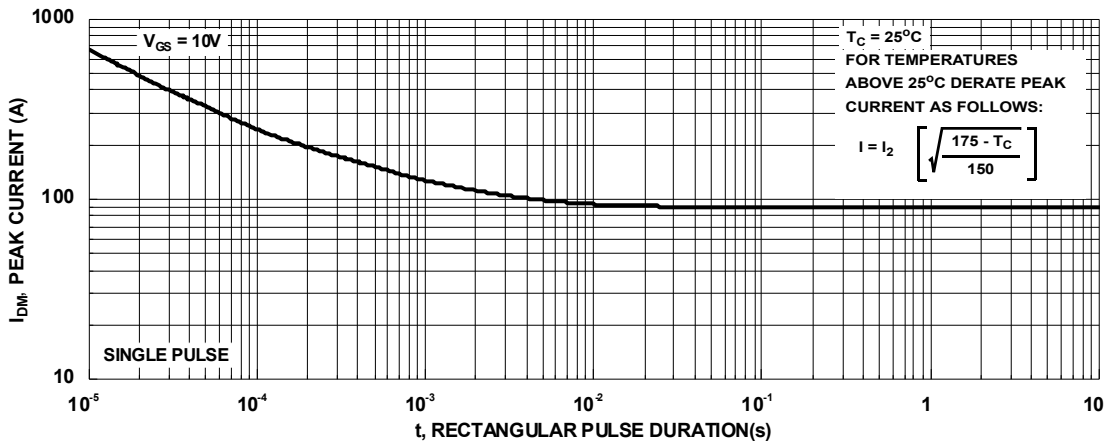


Figure 4. Peak Current Capability

## Typical Characteristics

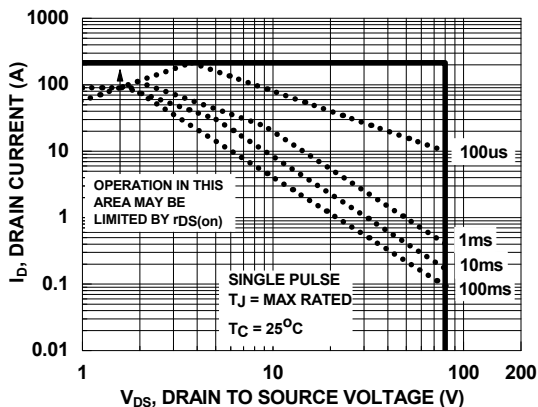
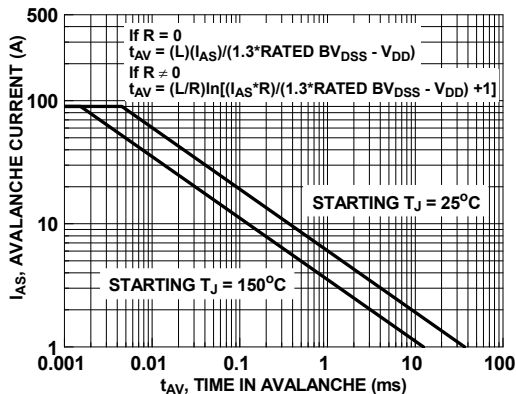


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

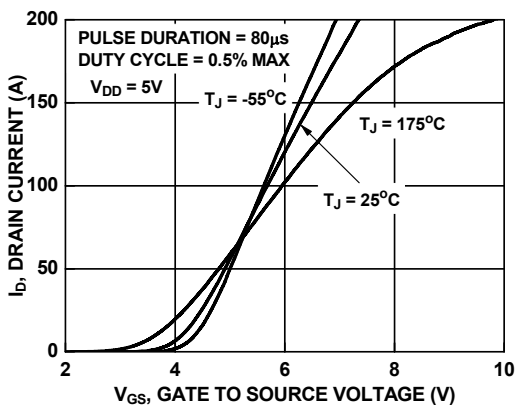


Figure 7. Transfer Characteristics

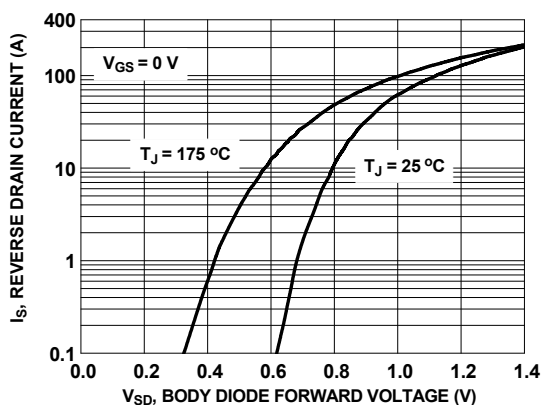


Figure 8. Forward Diode Characteristics

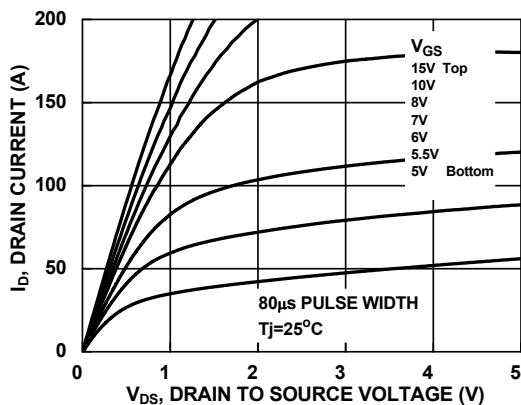


Figure 9. Saturation Characteristics

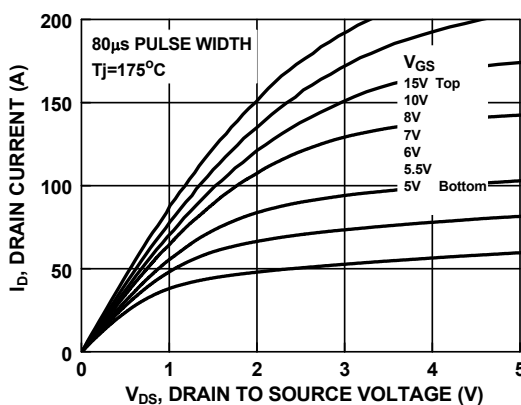


Figure 10. Saturation Characteristics

### Typical Characteristics

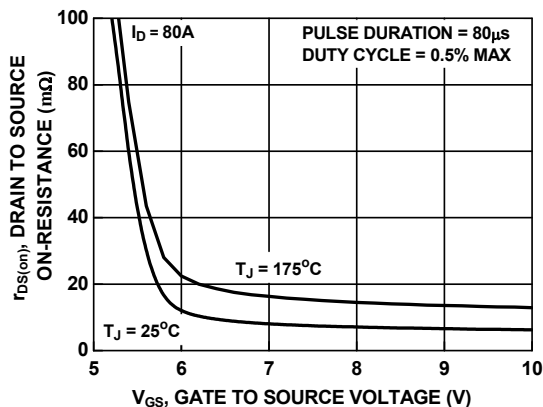


Figure 11.  $R_{DS(on)}$  vs. Gate Voltage

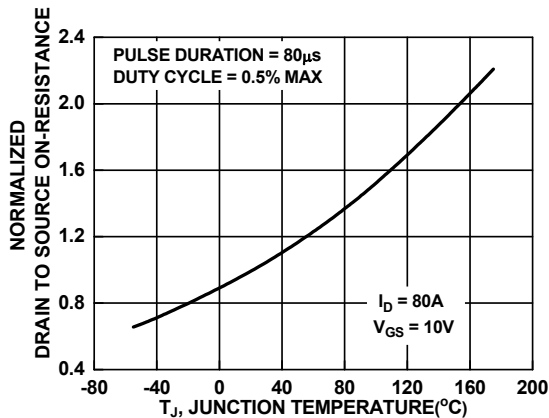


Figure 12. Normalized  $R_{DS(on)}$  vs. Junction Temperature

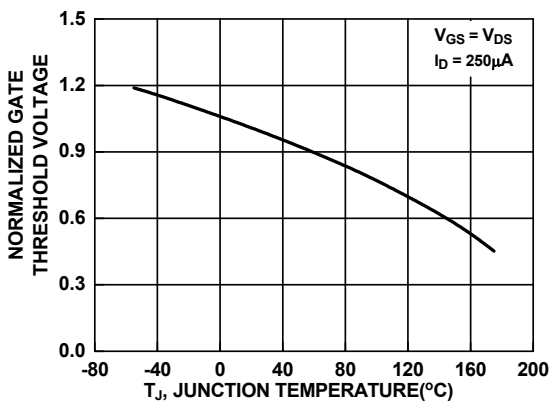


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

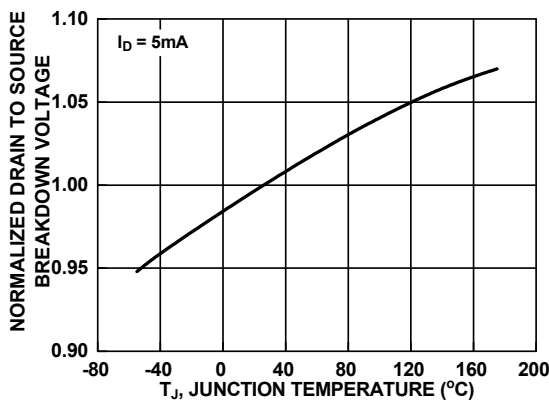


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

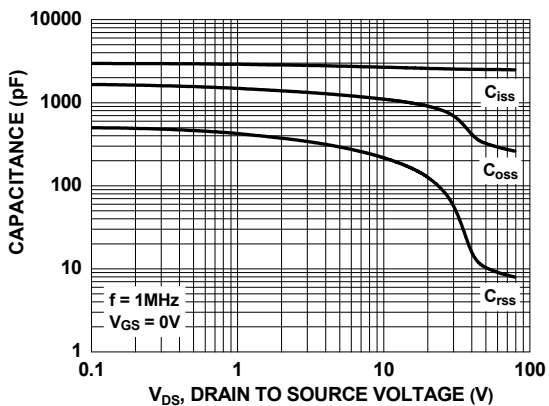


Figure 15. Capacitance vs. Drain to Source Voltage

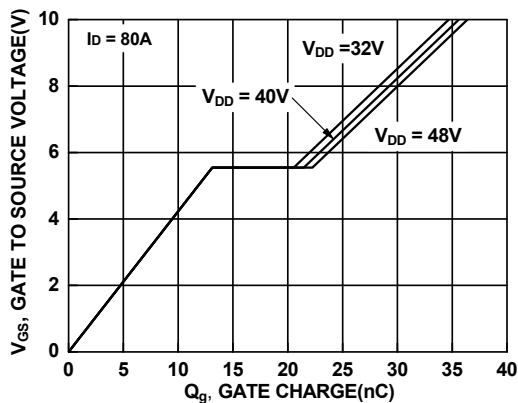
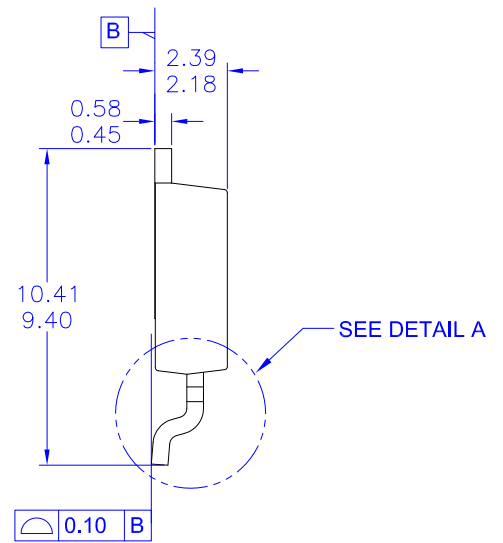
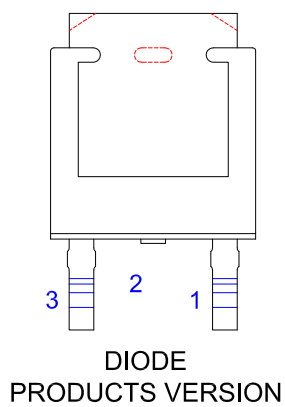


Figure 16. Gate Charge vs. Gate to Source Voltage



NOTES: UNLESS OTHERWISE SPECIFIED  
A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

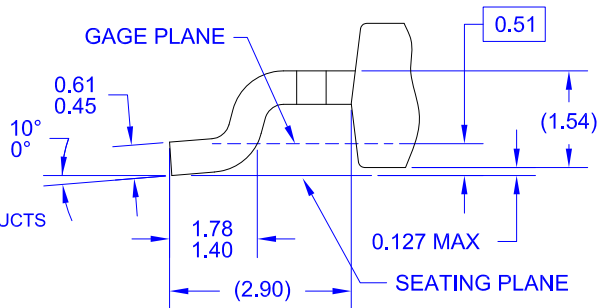
D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.

E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS

F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.

H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



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